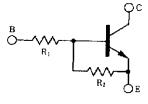


# COMPOUND TRANSISTOR BA1A3Q

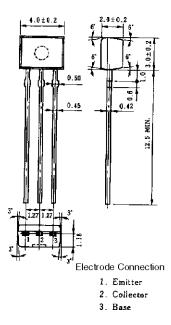
## on-chip resistor NPN silicon epitaxial transistor For mid-speed switching

#### FEATURES

On-chip bias resistor
 (R<sub>1</sub> = 1.0 kΩ, R<sub>2</sub> = 10 kΩ)



## PACKAGE DRAWING (UNIT: mm)



#### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Complementary transistor with BN1A3Q

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vсво	60	V
Collector to emitter voltage	VCEO	50	V
Emitter to base voltage	VEBO	5	V
Collector current (DC)	IC(DC)	100	mA
Collector current (Pulse)	IC(pulse) *	200	mA
Total power dissipation	Р⊤	250	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

\* PW  $\leq$  10 ms, duty cycle  $\leq$  50 %

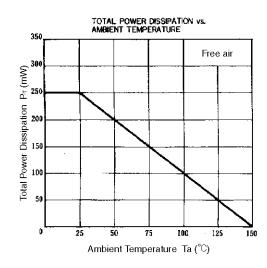
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

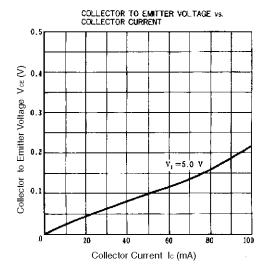
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = 50 \text{ V}, \text{ I}_{E} = 0$			100	nA
DC current gain	hfe1 **	Vce = 5.0 V, Ic = 5.0 mA	35	60	100	-
DC current gain	hfe2 **	Vce = 5.0 V, Ic = 50 mA	80	230		-
Collector saturation voltage	V <sub>CE(sat)</sub> **	Ic = 5.0 mA, I <sub>B</sub> = 0.25 mA		0.05	0.2	V
Low level input voltage	VIL **	$V_{CE} = 5.0 \text{ V}, \text{ Ic} = 100 \ \mu\text{A}$		0.7	0.5	V
High level input voltage	VIH **	$V_{CE} = 0.2 \text{ V}, \text{ Ic} = 5.0 \text{ mA}$	2.0	1.0		V
Input resistance	R1		0.7	1.0	1.3	kΩ
E-to-B resistance	R <sub>2</sub>		7	10	13	kΩ
Turn-on time	ton	$V_{CC} = 5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega$			0.2	μs
Storage time	tstg	Vι = 5 V, PW = 2 μs			5.0	μs
Turn-off time	toff	duty cycle≤2 %			6.0	μs

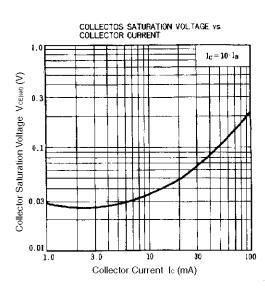
\*\* PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2 %

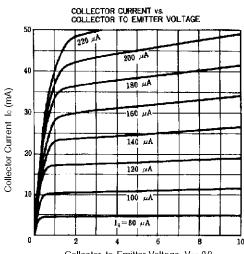
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### TYPICAL CHARACTERISTICS (Ta = 25°C)

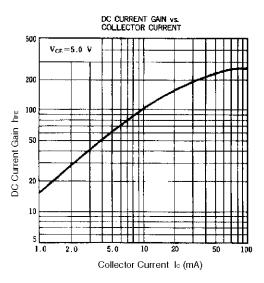


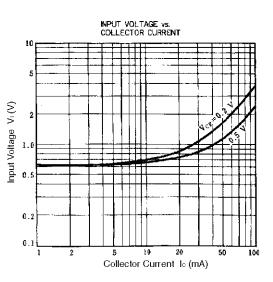


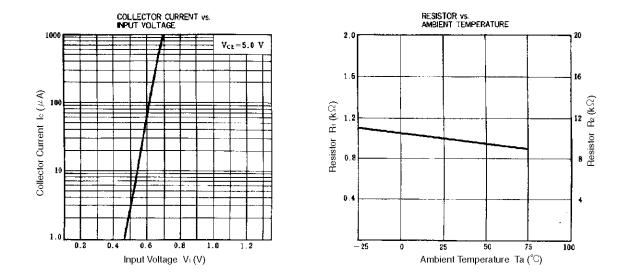




Collector to Emitter Voltage Vc∈ (V)







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